

MOSFET – Power, N-Channel, Dual ECH8

30 V, 8 A, 20.5 m Ω

ECH8663R

- Low ON-resistance
- 2.5 V Drive
- Common-drain Type
- Protection Diode in
- Built-in Gate Protection Resistor
- Best Suited for LiB Charging and Discharging Switch
- Halogen Free Compliance

Specifications

ABSOLUTE MAXIMUM RATINGS (at Ta = 25°C)

Parameter	Symbol	Conditions	Ratings	Unit	
Drain-to-Source Voltage	V _{DSS}		30	V	
Gate-to-Source Voltage	V_{GSS}		±12	V	
Drain Current (DC)	I _D		8	Α	
Drain Current (Pulse)	I _{DP}	PW ≤ 10 μs, duty cycle ≤ 1%	60	Α	
Allowable Power Dissipation	P _D	When mounted on ceramic substrate (900 mm ² × 0.8 mm) 1 unit	1.4	W	
Total Power Dissipation	P _T	When mounted on ceramic substrate (900 mm ² × 0.8 mm)	1.5	W	
Channel Temperature	Tch		150	°C	
Storage Temperature	Tstg		-55 to +150	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

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V _{DSS}	R _{DS} (on) MAX	I _D MAX
30 V	20.5 mΩ @ 4.5 V	8 A
	21 mΩ @ 4.0 V	
	23 mΩ @ 3.1 V	
	28 mΩ @ 2.5 V	

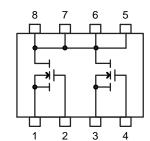


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MARKING DIAGRAM



ELECTRICAL CONNECTION



- 1: Source 1
- 2: Gate 1
- 3: Source 2
- 4: Gate 2
- 5: Drain
- 6: Drain 7: Drain
- 8: Drain

ORDERING INFORMATION

	Device	Package	Shipping [†]
E	ECH8663R-TL-H	SOT-28FL / ECH8 (Pb-Free and Halide Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (at Ta = 25°C)

			Ratings			
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_	_	V
Zero-Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	-	_	1	μΑ
Gate-to-Source Leakage Current	I _{GSS}	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±10	μΑ
Cutoff Voltage	V _{GS} (off)	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$	0.5	_	1.3	V
Forward Transfer Admittance	yfs	V _{DS} = 10 V, I _D = 4 A	5	8.5	_	S
Static Drain-to-Source On-State	R _{DS} (on)1	I _D = 4 A, V _{GS} = 4.5 V	10.5	15.5	20.5	mΩ
Resistance Static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D = 4 A, V _{GS} = 4.0 V	11	16	21	mΩ
	R _{DS} (on)3	I _D = 2 A, V _{GS} = 3.1 V	12	17.5	23	mΩ
	R _{DS} (on)4	I _D = 2 A, V _{GS} = 2.5 V	12	20	28	mΩ
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.	-	320	_	ns
Rise Time	t _r		-	850	_	ns
Turn-OFF Delay Time	t _d (off)		-	4200	_	ns
Fall Time	t _f		-	1800	_	ns
Total Gate Charge	Qg	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V},$	-	12.3	_	nC
Gate-to-Source Charge	Qgs	I _D = 8 A	-	2.4	-	nC
Gate-to-Drain "Miller" Charge	Qgd	1	-	2.8	-	nC
Diode Forward Voltage	V _{SD}	I _S = 8 A, V _{GS} = 0 V	-	0.75	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit

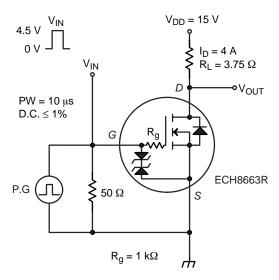
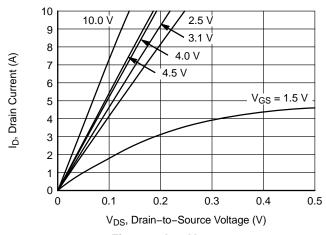


Figure 1. Switching Time Test Circuit

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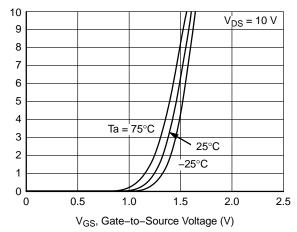


Figure 2. $I_D - V_{DS}$

Figure 3. I_D - V_{GS}

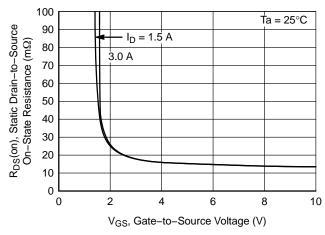


Figure 4. R_{DS}(on) - V_{GS}

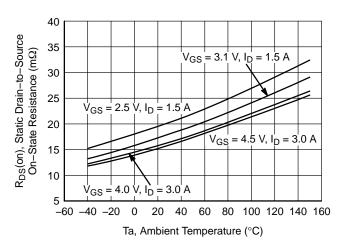


Figure 5. R_{DS}(on) - Ta

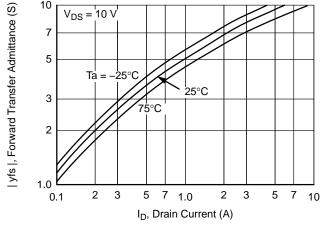


Figure 6. | yfs | - ID

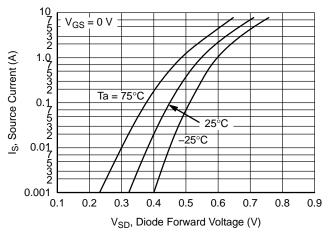


Figure 7. I_S - V_{SD}

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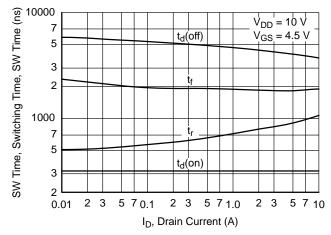


Figure 8. SW Time - I_D

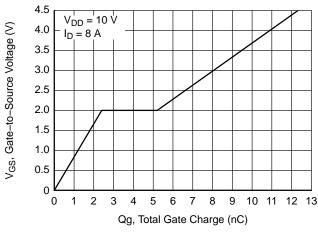


Figure 9. V_{GS} – Qg

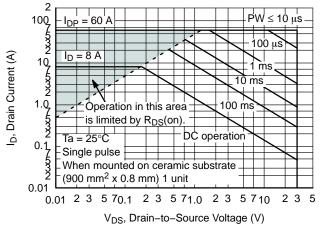


Figure 10. ASO

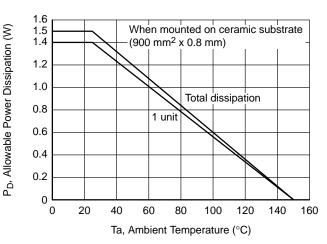
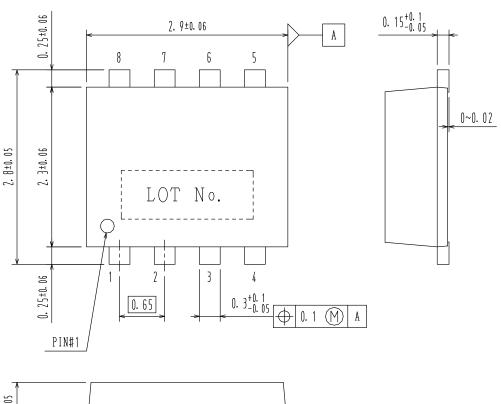
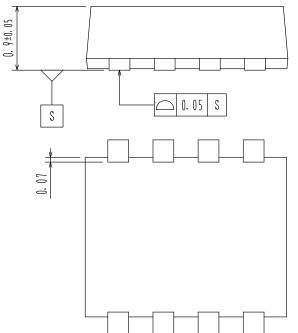


Figure 11. P_D – Ta

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